2-input NAND gate

74AHC1G00; 74AHCT1G00

FEATURES

- Symmetrical output impedance
- High noise immunity
- ESD protection:
  HBM EIA/JESD22-A114-A
  Exceeds 2000 V
  MM EIA/JESD22-A115-A Exceeds
  200 V
- Low power dissipation
- Balanced propagation delays
- Very small 5 pin package
- Output capability: standard.

DESCRIPTION

The 74AHC1G/AHCT1G00 is a high-speed Si-gate CMOS device.

The 74AHC1G/AHCT1G00 provides the 2-input NAND function.

FUNCTION TABLE

See note 1.

INPUTS		OUTPUT
inA	inB	outY
L	L	H
L	H	H
H	L	H
H	H	L

Note

1. H = HIGH voltage level.
   L = LOW voltage level.

QUICK REFERENCE DATA

GND = 0 V; T_{amb} = 25 °C; t_r = t_f ≤ 3.0 ns.

SYMBOL	PARAMETER	CONDITIONS	TYPICAL		UNIT
			AHC1G	AHCT1G	
t_{PHL}/t_{PLH}	propagation delay inA, inB to outY	C_L = 15 pF V_{CC} = 5 V	2.9	2.8	ns
C_I	input capacitance		1.5	1.5	pF
C_{PD}	power dissipation capacitance	notes 1 and 2; C_L = 50 pF; f = 1 Mhz	10	12	pF

Notes

1. C_{PD} is used to determine the dynamic power dissipation (P_D in µW).

   a) $P_D = C_{PD} \times V_{CC}^2 \times f_i + (C_L \times V_{CC}^2 \times f_o)$ where:

   b) f_i = input frequency in MHz;

   c) f_o = output frequency in MHz;

   d) C_L = output load capacitance in pF;

   e) V_{CC} = supply voltage in V.

2. The condition is V_I = GND to V_{CC}.

PINNING

PIN	SYMBOL	DESCRIPTION
1	inB	data input
2	inA	data input
3	GND	ground (0 V)
4	outY	data output
5	V_{CC}	DC supply voltage

ORDERING AND PACKAGE INFORMATION

TYPE NUMBER	PACKAGES					
	TEMPERATURE RANGE	PINS	PACKAGE	MATERIAL	CODE	MARKING
74AHC1G00GW	−40 °C to +85 °C	5	SC-88A	plastic	SOT353	AA
74AHCT1G00GW		5	SC-88A	plastic	SOT353	CA

2-input NAND gate

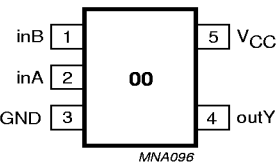74AHC1G00; 74AHCT1G00

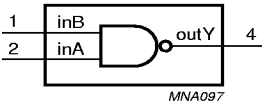Fig.1 Pin configuration.

Fig.2 Logic symbol.

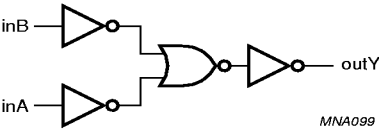Fig.3 IEC logic symbol.

Fig.4 Logic diagram.

2-input NAND gate

74AHC1G00; 74AHCT1G00

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	74AHC1G			74AHCT1G			UNIT
			MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
V_{CC}	DC supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
V_I	Input voltage		0	–	5.5	0	–	5.5	V
V_O	output voltage		0	–	V_{CC}	0	–	V_{CC}	V
T_{amb}	operating ambient temperature range	see DC and AC characteristics per device	–40	+25	+85	–40	+25	+85	°C
t_r, t_f ($\Delta t/\Delta f$)	input rise and fall times except for Schmitt-trigger inputs	V_{CC} = 3.3 V ±0.3 V	–	–	100	–	–	–	ns/V
		V_{CC} = 5 V ±0.5 V	–	–	20	–	–	20	

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134); voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CC}	DC supply voltage		–0.5	+7.0	V
V_I	Input voltage range		–0.5	+7.0	V
I_{IK}	DC input diode current	$V_I < -0.5$	–	–20	mA
I_{OK}	DC output diode current	$V_O < -0.5$ or $V_O > V_{CC} + 0.5$ V; note 1	–	±20	mA
I_O	DC output source or sink current	-0.5 V $< V_O < V_{CC} + 0.5$ V	–	±25	mA
I_{CC}	DC V_{CC} or GND current		–	±75	mA
T_{stg}	storage temperature range		–65	+150	°C
P_D	power dissipation per package	temperature range: –40 to +85 °C; note 2	–	200	mW

Notes

1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

2. Above +55 °C the value of P_D derates linearly with 2.5 mW/K.

2-input NAND gate

74AHC1G00; 74AHCT1G00

DC CHARACTERISTICS

Family 74AHC1G

Over recommended operating conditions; voltage are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	TEST CONDITIONS		T_{amb} (°C)					UNIT
		OTHER	V_{CC} (V)	+25			−40 to +85		
				MIN.	TYP.	MAX.	MIN.	MAX.	
V_{IH}	HIGH-level input voltage		2.0	1.5	–	–	1.5	–	V
			3.0	2.1	–	–	2.1	–	
			5.5	3.85	–	–	3.85	–	
V_{IL}	LOW-level input voltage		2.0	–	–	0.5	–	0.5	V
			3.0	–	–	0.9	–	0.9	
			5.5	–	–	1.65	–	1.65	
V_{OH}	HIGH-level output voltage; all outputs	$V_I = V_{IH}$ or V_{IL}; $I_O = −50$ μA	2.0	1.9	2.0	–	1.9	–	V
			3.0	2.9	3.0	–	2.9	–	
			4.5	4.4	4.5	–	4.4	–	
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}; $I_O = −4.0$ mA	3.0	2.58	–	–	2.48	–	V
		$V_I = V_{IH}$ or V_{IL}; $I_O = −8.0$ mA	4.5	3.94	–	–	3.8	–	
V_{OL}	LOW-level output voltage; all outputs	$V_I = V_{IH}$ or V_{IL}; $I_O = 50$ μA	2.0	–	0	0.1	–	0.1	V
			3.0	–	0	0.1	–	0.1	
			4.5	–	0	0.1	–	0.1	
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}; $I_O = 4$ mA	3.0	–	–	0.36	–	0.44	V
		$V_I = V_{IH}$ or V_{IL}; $I_O = 8$ mA	4.5	–	–	0.36	–	0.44	
I_I	input leakage current	$V_I = V_{CC}$ or GND	5.5	–	–	0.1	–	1.0	μA
I_{CC}	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0$	5.5	–	–	1.0	–	10	μA
C_I	input capacitance			–	1.5	10	–	10	pF

2-input NAND gate

74AHC1G00; 74AHCT1G00

Family 74AHCT1G

Over recommended operating conditions; voltage are referenced to GND (ground = 0 V).

| SYMBOL | PARAMETER | TEST CONDITIONS | | T_{amb} (°C) | | | | | UNIT |
| | | OTHER | V_{CC} (V) | +25 | | | −40 to +85 | | |
				MIN.	TYP.	MAX.	MIN.	MAX.	
V_{IH}	HIGH-level input voltage		4.5 to 5.5	2.0	–	–	2.0	–	V
V_{IL}	LOW-level input voltage		4.5 to 5.5	–	–	0.8	–	0.8	V
V_{OH}	HIGH-level output voltage; all outputs	$V_I = V_{IH}$ or V_{IL}; $I_O = -50$ μA	4.5	4.4	4.5	–	4.4	–	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}; $I_O = -8.0$ mA	4.5	3.94	–	–	3.8	–	V
V_{OL}	LOW-level output voltage; all outputs	$V_I = V_{IH}$ or V_{IL}; $I_O = 50$ μA	4.5	–	0	0.1	–	0.1	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}; $I_O = 8$ mA	4.5	–	–	0.36	–	0.44	V
I_I	input leakage current	$V_I = V_{IH}$ or V_{IL}	5.5	–	–	0.1	–	1.0	μA
I_{CC}	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0$	5.5	–	–	1.0	–	10	μA
ΔI_{CC}	additional quiescent supply current per input pin	$V_I = 3.4$ V other inputs at V_{CC} or GND; $I_O = 0$	5.5	–	–	1.35	–	1.5	mA
C_I	input capacitance			–	1.5	10	–	10	pF

2-input NAND gate

74AHC1G00; 74AHCT1G00

AC CHARACTERISTICS

Type 74AHC1G00

GND = 0 V; t_r = t_f ≤ 3.0 ns.

SYMBOL	PARAMETER	TEST CONDITIONS			T_{amb} (°C)					UNIT
		WAVEFORMS	C_L	V_{CC} (V)	+25			−40 to +85		
					MIN.	TYP.	MAX.	MIN.	MAX.	
t_{PHL}/t_{PLH}	propagation delay inA, inB to outY	see Figs 5 and 6	15 pF	3.0 to 3.6	−	4.1[1]	7.9	1.0	9.5	ns
t_{PHL}/t_{PLH}	propagation delay inA, inB to outY	see Figs 5 and 6	50 pF	3.0 to 3.6	−	5.8[1]	11.4	1.0	13.0	ns
t_{PHL}/t_{PLH}	propagation delay inA, inB to outY	see Figs 5 and 6	15 pF	4.5 to 5.5	−	2.9[2]	5.5	1.0	6.5	ns
t_{PHL}/t_{PLH}	propagation delay inA, inB to outY	see Figs 5 and 6	50 pF	4.5 to 5.5	−	4.2[2]	7.5	1.0	8.5	ns

Notes

1. Typical values at V_{CC} = 3.3 V.

2. Typical values at V_{CC} = 5.0 V.

Type 74AHCT1G00

GND = 0 V; t_r = t_f ≤ 3.0 ns.

SYMBOL	PARAMETER	TEST CONDITIONS			T_{amb} (°C)					UNIT
		WAVEFORMS	C_L	V_{CC} (V)	+25			−40 to +85		
					MIN.	TYP.	MAX.	MIN.	MAX.	
t_{PHL}/t_{PLH}	propagation delay inA, inB to outY	see Figs 5 and 6	15 pF	4.5 to 5.5	−	2.8[1]	6.9	1.0	8.0	ns
t_{PHL}/t_{PLH}	propagation delay inA, inB to outY	see Figs 5 and 6	50 pF	4.5 to 5.5	−	4.2[1]	7.9	1.0	9.0	ns

Note

1. Typical values at V_{CC} = 5.0 V.

2-input NAND gate

74AHC1G00; 74AHCT1G00

AC WAVEFORMS

FAMILY	V_I INPUT REQUIREMENTS	V_M INPUT	V_M OUTPUT
AHC1G	GND to V_{CC}	50% V_{CC}	50% V_{CC}
AHCT1G	GND to 3.0 V	1.5 V	50% V_{CC}

Fig.5   The input (inA, inB) to output (outY) propagation delays.

Definitions for test circuit:

C_L = Load capacitance including jig and probe capacitance (see Chapter "AC Characteristics").

R_T = Termination resistance should be equal to the output impedance Z_0 of the pulse generator.

Fig.6 Load circuitry for switching times.

2-input NAND gate

74AHC1G00; 74AHCT1G00

PACKAGE OUTLINE

Plastic surface mounted package; 5 leads

SOT353

scale

DIMENSIONS (mm are the original dimensions)

UNIT	A	A$_1$ max	b$_p$	c	D	E $^{(2)}$	e	e$_1$	H$_E$	L$_p$	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT353			SC-88A			97-02-28
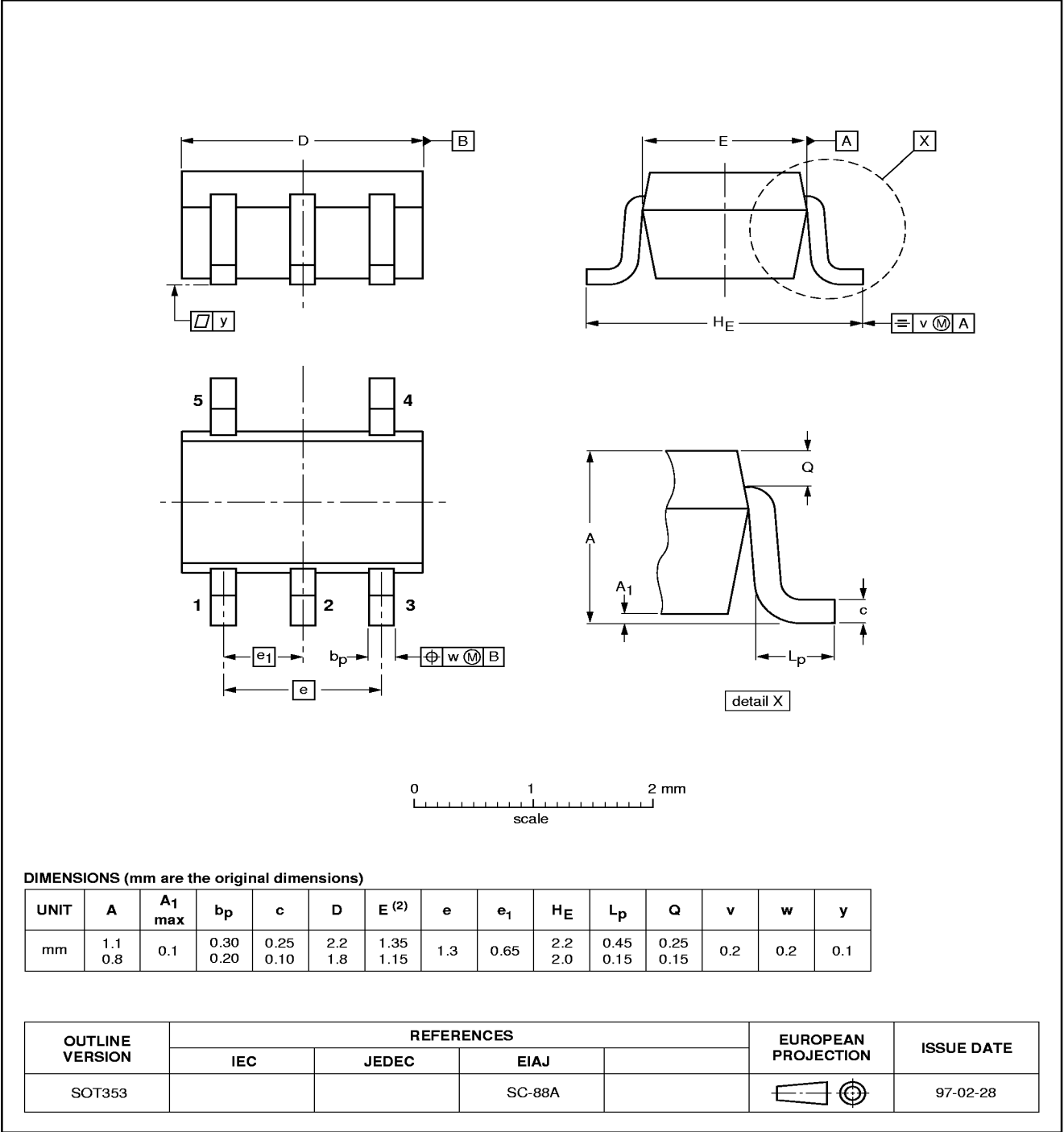
2-input NAND gate   **74AHC1G00; 74AHCT1G00**

SOLDERING

Introduction to soldering surface mount packages

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"Data Handbook IC26; Integrated Circuit Packages"* (document order number 9398 652 90011).

There is no soldering method that is ideal for all surface mount IC packages. Wave soldering is not always suitable for surface mount ICs, or for printed-circuit boards with high population densities. In these situations reflow soldering is often used.

Reflow soldering

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several methods exist for reflowing; for example, infrared/convection heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 250 °C. The top-surface temperature of the packages should preferable be kept below 230 °C.

Wave soldering

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
  - larger than or equal to 1.27 mm, the footprint longitudinal axis is **preferred** to be parallel to the transport direction of the printed-circuit board;
  - smaller than 1.27 mm, the footprint longitudinal axis **must** be parallel to the transport direction of the printed-circuit board.

  The footprint must incorporate solder thieves at the downstream end.
- For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time is 4 seconds at 250 °C.
A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

Manual soldering

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C.

When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 °C.

2-input NAND gate

74AHC1G00; 74AHCT1G00

Suitability of surface mount IC packages for wave and reflow soldering methods

PACKAGE	SOLDERING METHOD	
	WAVE	**REFLOW**[1]
BGA, SQFP	not suitable	suitable
HLQFP, HSQFP, HSOP, SMS	not suitable[2]	suitable
PLCC[3], SO, SOJ	suitable	suitable
LQFP, QFP, TQFP	not recommended[3][4]	suitable
SSOP, TSSOP, VSO	not recommended[5]	suitable

Notes

1. All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the *"Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods"*.

2. These packages are not suitable for wave soldering as a solder joint between the printed-circuit board and heatsink (at bottom version) can not be achieved, and as solder may stick to the heatsink (on top version).

3. If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.

4. Wave soldering is only suitable for LQFP, TQFP and QFP packages with a pitch (e) equal to or larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.

5. Wave soldering is only suitable for SSOP and TSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.